

T M Al Tahtamouni

List of Publications by Year in descending order

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619
citing authors

#	ARTICLE	IF	CITATIONS
1	Revealing microstructure and dislocation behavior in BAlN/AlGa _N heterostructures. Applied Physics Express, 2018, 11, 011001.	2.4	8
2	Influence of TMAI preflow on AlN epitaxy on sapphire. Applied Physics Letters, 2017, 110, 192106.	3.3	22
3	Structural properties, crystal quality and growth modes of MOCVD-grown AlN with TMAI pretreatment of sapphire substrate. Journal Physics D: Applied Physics, 2017, 50, 395101.	2.8	13
4	Dramatic enhancement of 1.54-μm emission in Er doped GaN quantum well structures. Applied Physics Letters, 2015, 106, 121106.	3.3	13
5	Effects of Mg-doped AlN/AlGa _N superlattices on properties of p-GaN contact layer and performance of deep ultraviolet light emitting diodes. AIP Advances, 2014, 4, 047122.	1.3	20
6	Effects of double layer AlN buffer layers on properties of Si-doped Al _x Ga _{1-x} N for improved performance of deep ultraviolet light emitting diodes. Journal of Applied Physics, 2013, 113, 123501.	2.5	20
7	Surfactant effects of gallium on quality of AlN epilayers grown via metal-organic chemical-vapour deposition on SiC substrates. Journal Physics D: Applied Physics, 2012, 45, 285103.	2.8	12
8	High quality AlN grown on double layer AlN buffers on SiC substrate for deep ultraviolet photodetectors. Applied Physics Letters, 2012, 101, .	3.3	19
9	Optical polarization in c-plane Al-rich Al _x Al _{1-x} Ga _{1-x} N single quantum wells. Applied Physics Letters, 2012, 101, 042103.	3.3	44
10	AlN MSM and Schottky photodetectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2148-2151.	0.8	13
11	Si-doped high Al-content AlGa _N epilayers with improved quality and conductivity using indium as a surfactant. Applied Physics Letters, 2008, 92, .	3.3	36
12	Beryllium acceptor binding energy in AlN. Applied Physics Letters, 2008, 93, .	3.3	15
13	Photoluminescence properties of AlN homoepilayers with different orientations. Applied Physics Letters, 2008, 93, .	3.3	28
14	Growth and photoluminescence studies of a-plane Al _x Ga _{1-x} N quantum wells. Applied Physics Letters, 2007, 90, 221105.	3.3	19
15	Correlation between biaxial stress and free exciton transition in AlN epilayers. Applied Physics Letters, 2007, 91, 121117.	3.3	35
16	AlN avalanche photodetectors. Applied Physics Letters, 2007, 91, .	3.3	44
17	Hybrid AlN/SiC deep ultraviolet Schottky barrier photodetectors. Applied Physics Letters, 2007, 90, 263505.	3.3	45
18	Growth and photoluminescence studies of Al-rich Al _x Ga _{1-x} N quantum wells. Applied Physics Letters, 2006, 89, 131922.	3.3	31